

# MPSW92

## One Watt High Voltage Transistor

### PNP Silicon

#### Features

- Pb-Free Packages are Available\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	-300	Vdc
Collector – Base Voltage	$V_{CBO}$	-300	Vdc
Emitter – Base Voltage	$V_{EBO}$	-5.0	Vdc
Collector Current – Continuous	$I_C$	-500	mA <sub>dc</sub>
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.0 8.0	W mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	2.5 20	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

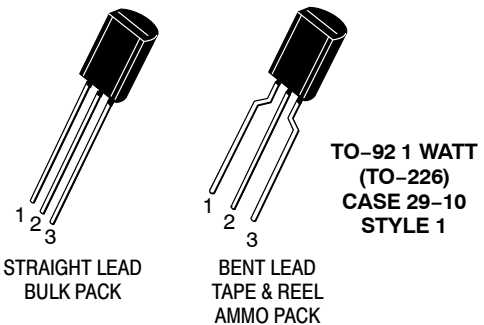
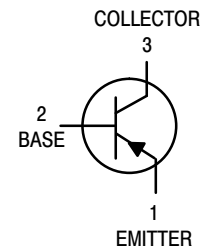
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

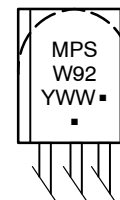


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#### MARKING DIAGRAM



MPSW45x = Device Code  
 x = 45A Devices  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# MPSW92

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (Note 1) (I <sub>C</sub> = –1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	–300	–	V <sub>dc</sub>
Collector–Base Breakdown Voltage (I <sub>C</sub> = –100 μA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	–300	–	V <sub>dc</sub>
Emitter–Base Breakdown Voltage (I <sub>E</sub> = –100 μA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	–5.0	–	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = –200 V <sub>dc</sub> , I <sub>E</sub> = 0)	I <sub>CBO</sub>	–	–0.25	μA <sub>dc</sub>
Emitter Cutoff Current (V <sub>EB</sub> = –3.0 V <sub>dc</sub> , I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	–0.1	μA <sub>dc</sub>

### ON CHARACTERISTICS (Note 1)

DC Current Gain (I <sub>C</sub> = –1.0 mA <sub>dc</sub> , V <sub>CE</sub> = –10 V <sub>dc</sub> ) (I <sub>C</sub> = –10 mA <sub>dc</sub> , V <sub>CE</sub> = –10 V <sub>dc</sub> ) (I <sub>C</sub> = –30 mA <sub>dc</sub> , V <sub>CE</sub> = –10 V <sub>dc</sub> )	h <sub>FE</sub>	25 40 25	– – –	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = –20 mA <sub>dc</sub> , I <sub>B</sub> = –2.0 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	–	–0.5	V <sub>dc</sub>
Base–Emitter Saturation Voltage (I <sub>C</sub> = –20 mA <sub>dc</sub> , I <sub>B</sub> = –2.0 mA <sub>dc</sub> )	V <sub>BE(sat)</sub>	–	–0.9	V <sub>dc</sub>

### SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I <sub>C</sub> = –10 mA <sub>dc</sub> , V <sub>CE</sub> = –20 V <sub>dc</sub> , f = 20 MHz)	f <sub>T</sub>	50	–	MHz
Collector–Base Capacitance (V <sub>CB</sub> = –20 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>cb</sub>	–	6.0	pF

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

### ORDERING INFORMATION

Device	Package	Shipping†
MPSW92	TO–92	5000 Units / Box
MPSW92G	TO–92 (Pb–Free)	5000 Units / Box
MPSW92RLREG	TO–92 (Pb–Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MPSW92

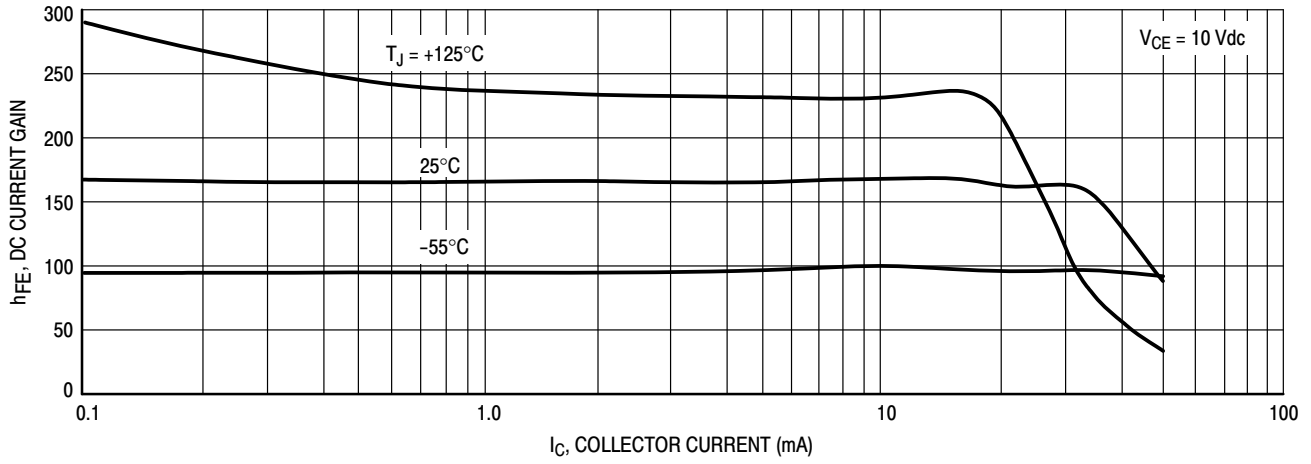


Figure 1. DC Current Gain

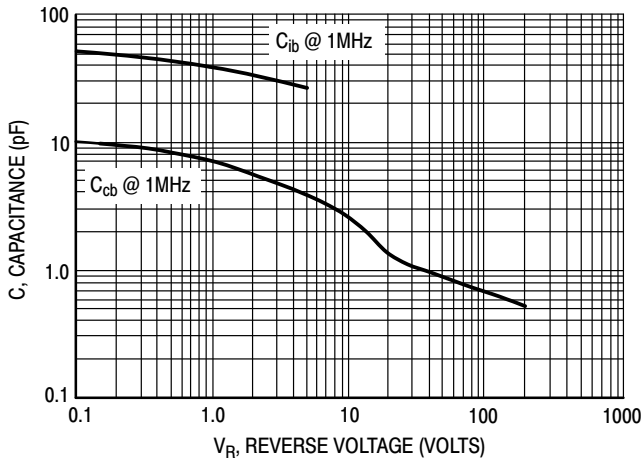


Figure 2. Capacitance

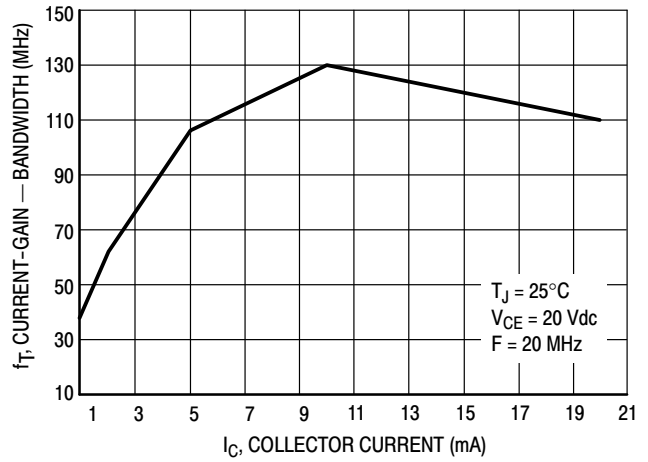


Figure 3. Current-Gain - Bandwidth

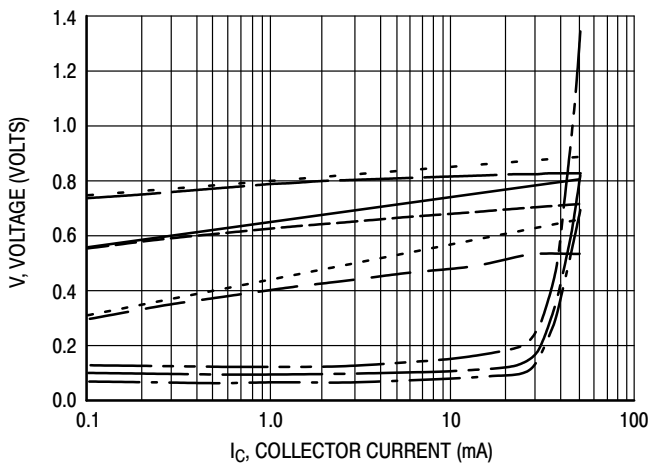


Figure 4. "ON" Voltages

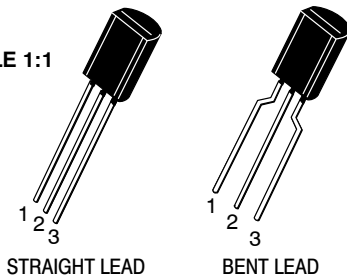
- $V_{CE(sat)}$  @  $25^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @  $125^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @  $-55^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $25^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $125^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $-55^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(on)}$  @  $25^\circ\text{C}$ ,  $V_{CE} = 10 \text{ V}$
- $V_{BE(on)}$  @  $125^\circ\text{C}$ ,  $V_{CE} = 10 \text{ V}$
- $V_{BE(on)}$  @  $-55^\circ\text{C}$ ,  $V_{CE} = 10 \text{ V}$

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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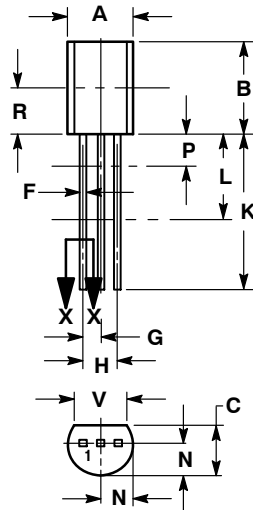


SCALE 1:1



TO-92 (TO-226) 1 WATT  
CASE 29-10  
ISSUE A

DATE 08 MAY 2012

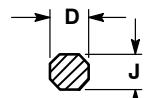


STRAIGHT LEAD

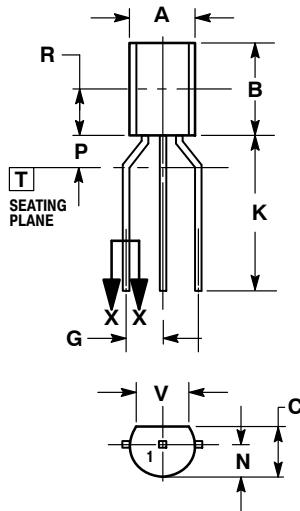
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---



SECTION X-X

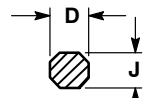


BENT LEAD

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
G	0.094	0.102	2.40	2.80
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---



SECTION X-X

STYLES ON PAGE 2

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**TO-92 (TO-226) 1 WATT  
CASE 29-10  
ISSUE A**

DATE 08 MAY 2012

STYLE 1:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 2:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 3:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 5:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 6:  
PIN 1. GATE  
2. SOURCE & SUBSTRATE  
3. DRAIN

STYLE 7:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 8:  
PIN 1. DRAIN  
2. GATE  
3. SOURCE & SUBSTRATE

STYLE 9:  
PIN 1. BASE 1  
2. EMITTER  
3. BASE 2

STYLE 10:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE & ANODE  
3. CATHODE

STYLE 12:  
PIN 1. MAIN TERMINAL 1  
2. GATE  
3. MAIN TERMINAL 2

STYLE 13:  
PIN 1. ANODE 1  
2. GATE  
3. CATHODE 2

STYLE 14:  
PIN 1. EMITTER  
2. COLLECTOR  
3. BASE

STYLE 15:  
PIN 1. ANODE 1  
2. CATHODE  
3. ANODE 2

STYLE 16:  
PIN 1. ANODE  
2. GATE  
3. CATHODE

STYLE 17:  
PIN 1. COLLECTOR  
2. BASE  
3. EMITTER

STYLE 18:  
PIN 1. ANODE  
2. CATHODE  
3. NOT CONNECTED

STYLE 19:  
PIN 1. GATE  
2. ANODE  
3. CATHODE

STYLE 20:  
PIN 1. NOT CONNECTED  
2. CATHODE  
3. ANODE

STYLE 21:  
PIN 1. COLLECTOR  
2. EMITTER  
3. BASE

STYLE 22:  
PIN 1. SOURCE  
2. GATE  
3. DRAIN

STYLE 23:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 24:  
PIN 1. EMITTER  
2. COLLECTOR/ANODE  
3. CATHODE

STYLE 25:  
PIN 1. MT 1  
2. GATE  
3. MT 2

STYLE 26:  
PIN 1. V<sub>CC</sub>  
2. GROUND 2  
3. OUTPUT

STYLE 27:  
PIN 1. MT  
2. SUBSTRATE  
3. MT

STYLE 28:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 29:  
PIN 1. NOT CONNECTED  
2. ANODE  
3. CATHODE

STYLE 30:  
PIN 1. DRAIN  
2. GATE  
3. SOURCE

STYLE 31:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 32:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER


STYLE 33:  
PIN 1. RETURN  
2. INPUT  
3. OUTPUT

STYLE 34:  
PIN 1. INPUT  
2. GROUND  
3. LOGIC

STYLE 35:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER

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